

General Description

Cremat's CR-110 is a single channel charge sensitive preamplifier module intended for use with various types of radiation detectors including semiconductor detectors (e.g. CdTe and CZT), p-i-n photodiodes, avalanche photodiodes (APDs), and various gas-based detectors. The CR-110 is one of a series of four charge sensitive preamplifiers offered by Cremat, which differ from each other most notably by their gain. A guide to selecting the best charge sensitive preamplifier for your application can be found at our web site: <http://cremat.com>. As with all Cremat's preamplifier modules, the CR-110 is small (less than one square inch in area), allowing for compact multichannel detection systems to be constructed using a modular design.

Detector coupling

The CR-110 can be used either in a direct coupled (DC) mode, or an AC coupled mode. If the detector current exceeds 10 nA, it is recommended that an AC coupled mode be used to prevent the resulting DC offset of the preamplifier output from saturating. Low frequency detector current (e.g. 'dark' current, or leakage current) produces an offset in the preamplifier output voltage at a rate of 0.2 V per nA. The use of AC coupling also is useful in improving the counting rate capability of the preamplifier. A schematic diagram of an AC-coupled charge sensitive preamplifier detection circuit can be found at http://www.cremat.com/CSP_application_notes.htm

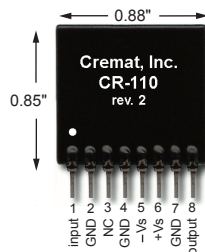


Figure 1

Package Specifications

The CR-110 circuit is contacted via an 8-pin SIP connection (0.100" spacing). Leads are 0.020 inches wide. Pin 1 is marked with a white dot for identification.

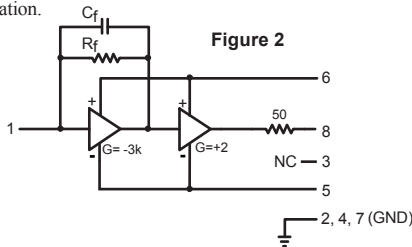


Figure 2

Equivalent circuit diagram

Figure 2 above shows a simplified equivalent circuit diagram of the CR-110, which is a two stage amplifier. The first stage is high gain, and the second stage is low gain with an emphasis on supplying sufficient output current to drive a terminated coaxial cable. Pin numbers corresponding with the CR-110 preamplifier are shown. R_f (100 M Ω) and C_f (1.4 pF) are the feedback resistor and capacitor respectively.

Output waveform

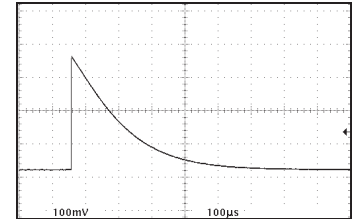
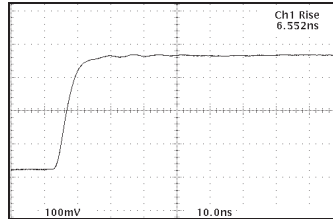
Charge sensitive preamplifiers are used when radiation is detected as a series of pulses, resulting in brief bursts of current flowing into or out of the preamplifier input. Depending on the type of detector, this burst of current may be very brief (<1 ns) or as long as a few μ s. For an idealized detection current pulse taking the form of a delta function, the detected charge (time integral of the input current) will ideally take the form of a step function.

The output waveform of an actual charge sensitive preamplifier will of course have a non-zero rise time: for the CR-110 this figure is

approximately 7 ns. Furthermore, capacitance at the preamplifier input (i.e. detector capacitance) will further slow the rise time at a rate of 0.4 ns / pF.

Keep in mind the output rise time will also be limited by the speed of the detector. For example, the detection current pulse from a CsI(Tl)/photodiode scintillation detector has a duration of approximately a couple μ s, so the expected rise time of the charge sensitive preamplifier output will be at least that long.

The output waveform of the CR-110 using a capacitively-coupled fast square wave pulser at the input is shown below to the left. At long time domains, the output decays due to the discharge of the feedback capacitor through the feedback resistor, with an RC time constant of 140 μ s. This decay of the output waveform is also shown below, to the right.



Cremat Inc, 950 Watertown St. #3
West Newton, MA 02465 USA
+1(617) 527-6590
FAX: +1(617) 527-2849
<http://cremat.com>



Specifications

Assume temp =20 °C, $V_s = \pm 6.1V$, unloaded output

	CR-110	units
Preamplification channels	1	
Equivalent noise charge (ENC)*		
ENC RMS	200	electrons
Equivalent noise in silicon	0.03	femtoCoul.
Equivalent noise in CdZnTe	1.7	keV (FWHM)
ENC slope	2.4	keV (FWHM)
Gain	4	elect. RMS /pF
Rise time **	1.4	volts / pC
Decay time constant	62	mV / MeV(Si)
Unsaturated output swing	7	ns
Maximum charge detectable per event	140	μ s
Power supply voltage (V_s)	-3 to +3	volts
maximum	1.3×10^7	electrons
minimum	2.1	pC
Power supply current (pos)	$V_s = \pm 13$	volts
(neg)	$V_s = \pm 6$	volts
Power dissipation	7.5	mA
Operating temperature	3.5	mA
Output offset	70	mW
Output impedance	-40 to +85	$^{\circ}$ C
	+0.2 to -0.2	volts
	50	ohms

* Measured with input unconnected, using Gaussian shaping amplifier with time constant =1 μ s. With a detector attached to the input, noise from the detector capacitance, leakage current, and dielectric losses will add to this figure.

** Pulse rise time (defined as the time to attain 90% of maximum value) has a linear relationship with input capacitance. Value cited in the table assumes zero added input capacitance. To calculate pulse rise time for practical situations, use the equation: $t_r = 0.4 C_d + 7$ ns, where t_r is the pulse rise time in ns, and C_d is the added capacitance (e.g. detector capacitance) in pF. Keep in mind that others factors within the detection system may further limit this value.